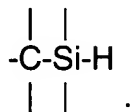


IN THE CLAIMS:

Please cancel claims 4, 14, 19, and 20 without prejudice, add new claim 21, and amend the claims as follows:

1. (Currently Amended) A method comprising depositing on a substrate a plurality of layers, wherein one or more of the layers is a low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising an organosilane compound and an oxidizing gas, the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, and a top layer of the plurality of layers is a photoresist.

2. (Currently Amended) The method of claim 1, wherein the low dielectric constant oxidized organosilane layer is deposited in the presence of RF power ~~from a mixture comprising an~~ and the organosilane compound ~~including~~ includes the structure:



3. (Original) The method of claim 2, wherein the organosilane compound is methylsilane.

4. (Canceled)

5. (Currently Amended) The method of claim ~~[[4]]~~ 1, wherein the oxidizing gas is N₂O.

6. (Original) The method of claim 2, wherein the organosilane compound includes the structure SiH_a(CH₃)_b(C₂H₅)_c(C₆H₅)_d, where a = 1 to 3, b = 0 to 3, c = 0 to 3, d = 0 to 3, and a+b+c+d = 4, or the structure Si₂H_e(CH₃)_f(C₂H₅)_g(C₆H₅)_h, where e = 1 to 5, f = 0 to 5, g = 0 to 5, h = 0 to 5, and e+f+g+h = 6.

7. (Currently Amended) The method of claim 1, wherein the ~~low dielectric constant oxidized organosilane layer is deposited in the presence of RF power from a mixture comprising an organosilane compound comprising~~ comprises an organo group selected from the group consisting of alkyl, aryl, alkenyl, and cyclohexenyl groups.

8. (Original) The method of claim 1, further comprising etching the low dielectric constant oxidized organosilane layer using fluorine, carbon, and oxygen ions.

9. (Original) The method of claim 1, further comprising etching a pattern in the plurality of the layers.

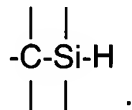
10. (Currently Amended) The method of claim 1, wherein ~~the dielectric constant~~ two of the layers are low dielectric constant oxidized organosilane layers ~~layer is about 3.0.~~

11. (Currently Amended) A method comprising depositing on a substrate a plurality of layers, wherein the plurality of layers comprises one low dielectric constant oxidized organosilane layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising an organosilane compound and an oxidizing gas and the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, a layer selected from the group consisting of parylene, FSG, and silicon oxide layers, and a top layer of the plurality of layers that is a photoresist.

12. (Currently Amended) The method of claim 11, wherein the low dielectric constant oxidized organosilane ~~etch-stop~~ layer is between two dielectric layers in the plurality of layers.

13. (Currently Amended) The method of claim 11, wherein the low dielectric constant oxidized organosilane ~~etch-stop~~ layer is deposited in the presence of RF power

from a mixture comprising an and the organosilane compound ~~including~~ includes the structure:



14. (Canceled)

15. (Currently Amended) A method comprising depositing on a substrate a plurality of layers, wherein ~~two~~ one or more of the layers ~~are~~ is a low dielectric constant oxidized organosilane ~~layers~~ layer comprising carbon, wherein the low dielectric constant oxidized organosilane layer is deposited in a plasma enhanced process from a mixture comprising a methylsilane compound and an oxidizing gas, the carbon content of the low dielectric constant oxidized organosilane layer is from 1% to 50% by atomic weight, and a top layer of the plurality of layers is a photoresist.

16. (Original) The method of claim 15, wherein the plurality of layers further comprises a layer selected from the group consisting of parylene, FSG, silicon oxide, and silicon nitride layers.

17. (Currently Amended) The method of claim 15, wherein the plurality of layers comprises two low dielectric constant oxidized organosilane layers and an etch stop layer adjacent both of the two low dielectric constant oxidized organosilane layers.

18. (Original) The method of claim 17, wherein the etch stop layer is a silicon oxide or silicon nitride layer.

19-20. (Canceled)

21. (New) The method of claim 15, wherein the methylsilane compound has the formula $\text{SiH}_n(\text{CH}_3)_{4-n}$, where $n=1$ to 3 or $\text{Si}_2\text{H}_m(\text{CH}_3)_{6-m}$, where $m=1$ to 5.